Discrete POWER & Signal **Technologies**

MPSL51

MPSL51

FAIRCHILD

SEMICONDUCTOR TM



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring high voltages. Sourced from Process 74. See 2N5401 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	100	V
V _{CBO}	Collector-Base Voltage	100	V
V_{EBO}	Emitter-Base Voltage	4.0	V
Ic	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	n Temperature Range -55 to +150 °C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Мах	Units	
		MPSL51		
P _D	Total Device Dissipation Derate above 25°C	625	mW mW/∘C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.0 83.3	°C/W	
R _{eJA}	Thermal Resistance, Junction to Ambient	200	°C/W	

PNP General Purpose Amplifi

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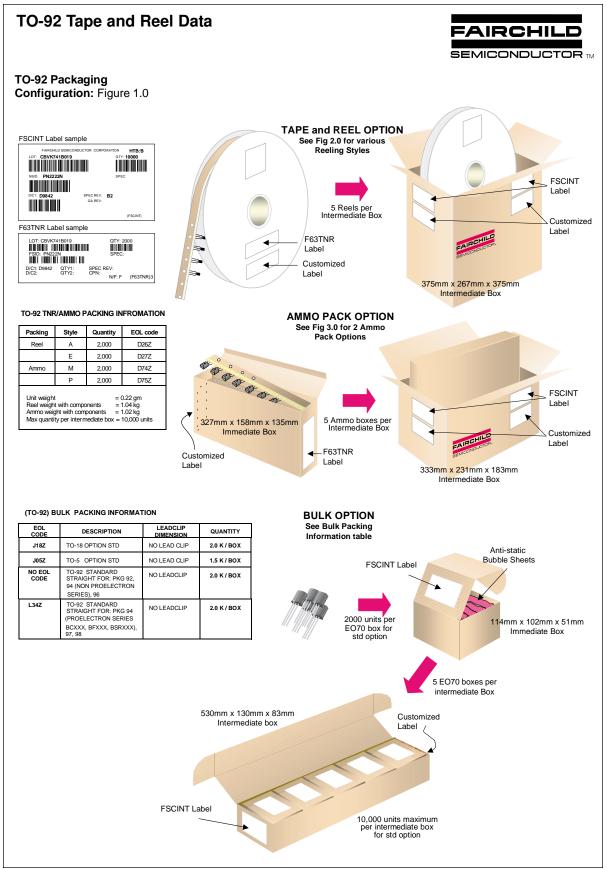
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Symbol	Parameter	Test Conditions	Min	Мах	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$	100		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$	100		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	4.0		V
I _{СВО}	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$		1.0	μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		100	nA
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$	40	250	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1.0 mA		0.25	V
		$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 30$ mA, $I_{\rm B} = 3.0$ mA $I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA $I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA	1	1.2	\uparrow
				1.2	V

SMALL SIGNAL CHARACTERISTICS

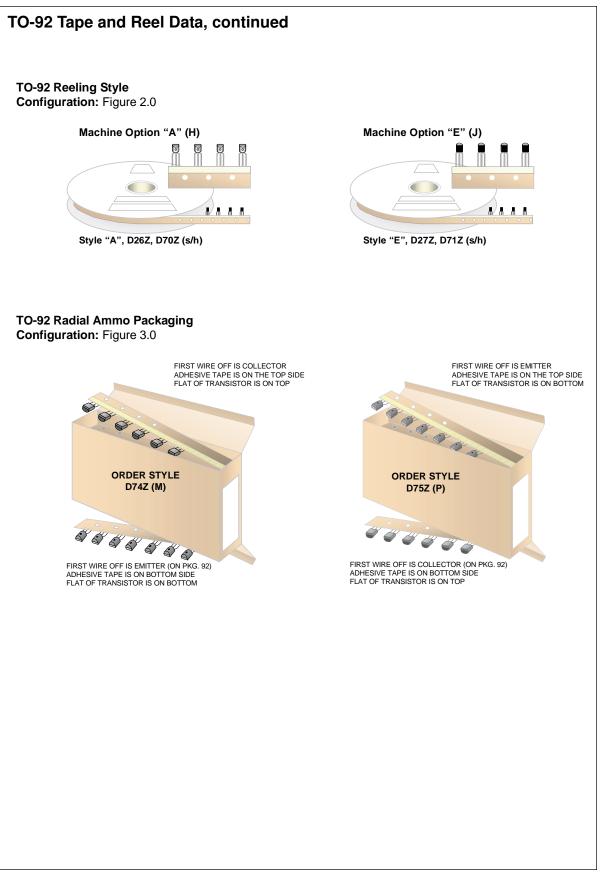
Cob	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		8.0	pF
h _{fe}	Small-Signal Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	20		
f _T	Current Gain - Bandwidth Product	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA},$	60		MHz

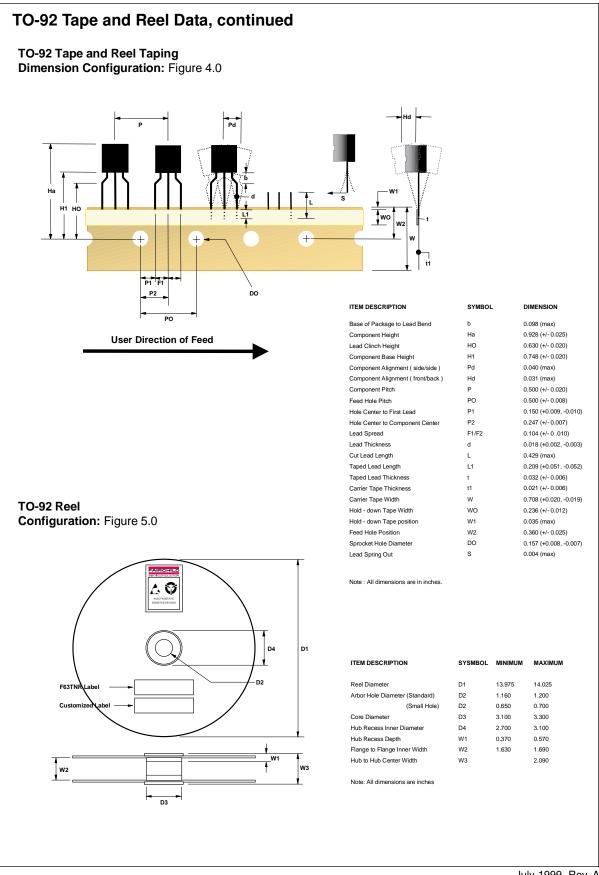
*Pulse Test: Pulse Width $\leq 300\,$ µs, Duty Cycle $\leq 2.0\%$



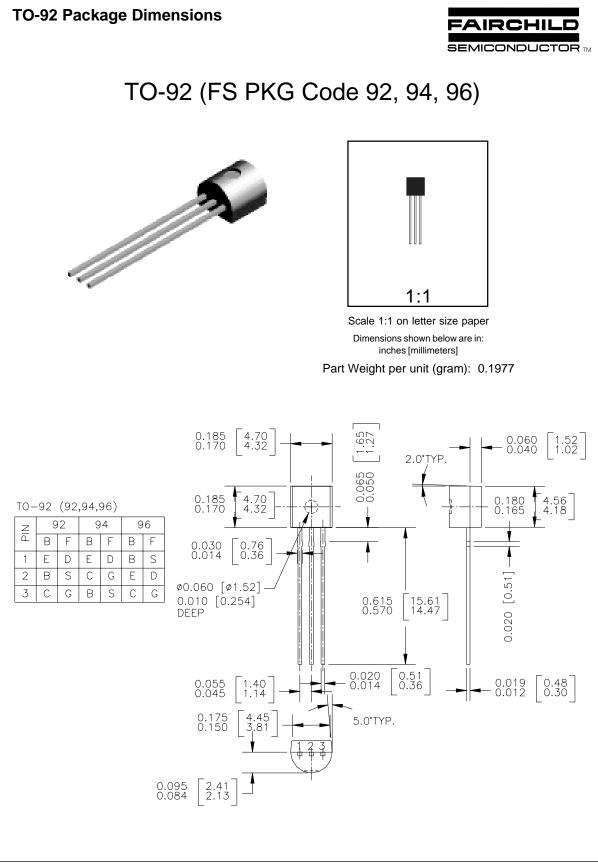
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Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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